	Туре	L #	Hits	Search Text	DBs	Time Stamp
1	BRS	L1	36	transducer same normal\$ adj2 thickness	USPAT	2001/08/07 12:44
2	BRS	L2	3	transducer same normal\$ adj2 thickness	US-PGP UB; EPO; JPO; DERWEN T; IBM TDB	2001/08/07 12:47
3	BRS	L3	15	normaliz\$ adj2 thick\$ and surface adj1 acoustic adj1 wave	US-PGP UB; EPO; JPO; DERWEN T; IBM TDB	2001/08/07 13:03
4	BRS	L4	31	normaliz\$ adj2 thick\$ and surface adj1 acoustic adj1 wave	USPAT	2001/08/07 13:04
5	BRS	L5	24	14 not 11	USPAT	2001/08/07 13:14
6	BRS	L6	0	.h/λ	USPAT	2001/08/07 13:14
7	BRS	L7	0	h/λ	USPAT	2001/08/07 13:14
8	BRS	L8	24	h/λ	US-PGP UB; EPO; JPO; DERWEN T; IBM TDB	2001/08/07 13:14

09/654/13

8/31/00

DERWENT-ACC-NO: 2001-355692

DERWENT-WEEK: 200142

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Elastic wave device where the substrate is turned about TITLE:

the X-axis of a

crystal

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MITSUBISHI DENKI KK[MITO] PATENT-ASSIGNEE:

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INT-CL (IPC): H03H009/145; H03H009/64

RELATED-ACC-NO: 2000-180552

ABSTRACTED-PUB-NO: WO 200137426A

BASIC-ABSTRACT: NOVELTY - An elastic wave device wherein the

surface of a

substrate is turned about the X-axis of a crystal of lithium

tantalate by an

angle of $3\overline{4-410}$ from the Y-axis of the crystal, the normalized

electrode

thickness (h/ lambda) determined by normalizing the thickness h

of at least a

part of the electrode fingers in an interdigital electrode with

the wavelength lambda of a surface acoustic wave is in the range of 0.01-0.05, and the duty ratio (w/p) of the electrode fingers determined by the width w and the arrangement pitch p of the electrode fingers is in the range of 0.6-1.0.

USE - Elastic wave device where the substrate is turned about the X-axis of a crystal

CHOSEN-DRAWING: Dwg.4/14

TITLE-TERMS:

ELASTIC WAVE DEVICE SUBSTRATE TURN AXIS CRYSTAL

DERWENT-CLASS: U25 V06

EPI-CODES: U25-B; V06-K03;

SECONDARY-ACC-NO:

Non-CPI Secondary Accession Numbers: N2001-258420